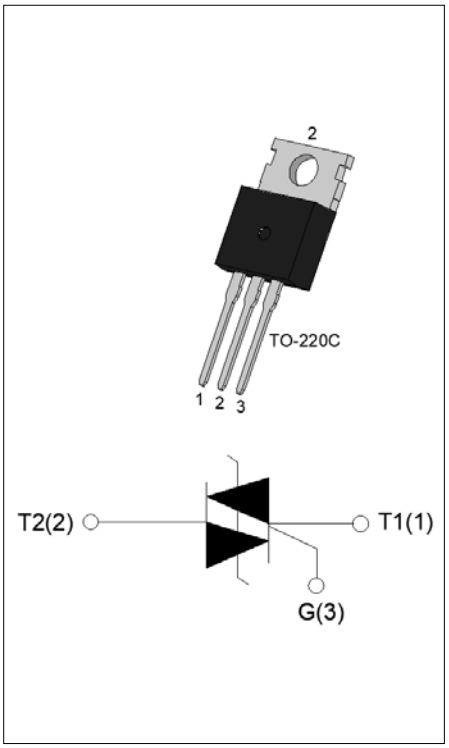
ACJT08C-800CW 8A TRIAC

Rev.A.1.1

DESCRIPTION:

The ACJT08C-800CW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The ACJT08C-800CW embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. Package TO-220C is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM} /V_{RRM}	800	V
$I_{GT\ I\ /\ II/III}$	35/35/35	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	℃
Operating junction temperature range	T_j	-40-125	℃
Repetitive peak off-state voltage (T_j=25℃)	V_{DRM}	800	V
Repetitive peak reverse voltage (T_j=25℃)	V_{RRM}	800	V
RMS on-state current (T_C≤108℃)	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle , t_p=20ms , T_j=25℃)	I_{TSM}	80	A
Non repetitive surge peak on-state current (full cycle , t_p=16.6ms , T_j=25℃)		88	
I^2t value for fusing (t_p=10ms , T_j=25℃)	I^2t	32	A^2s
Critical rate of rise of on-state current (I_G=2×I_{GT} , f=100Hz , T_j=125℃)	dI/dt	100	A/μs
Peak gate current (t_p=20μs , T_j=125℃)	I_{GM}	4	A
Average gate power dissipation (T_j=125℃)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W

Peak pulse voltage (T_j=25℃; non-repetitive,off-state;FIG.7)	V_{pp}	2.75	kV

ELECTRICAL CHARACTERISTICS (T_j=25℃ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	Ⅰ-Ⅱ-Ⅲ	MAX.	35	mA
V_{GT}		Ⅰ-Ⅱ-Ⅲ	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125℃ R_L =3.3kΩ	Ⅰ-Ⅱ-Ⅲ	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	Ⅰ-Ⅲ	MAX.	35	mA
		Ⅱ		55	
I_H	I_T =100mA		MAX.	30	mA
dV/dt	V_D=540V Gate Open T_j =125℃		MIN.	2600	V/μs
(dI/dt)c	(dV/dt)c=10V/μs, T_j=125℃		MIN.	10	A/ms
t_{on}	I_G=40mA I_A=200mA I_R=20mA T_j=25℃		TYP.	3	μs
t_{off}				30	
V_{CL}	I_{CL}=0.1mA t_p=1ms		MIN.	850	V

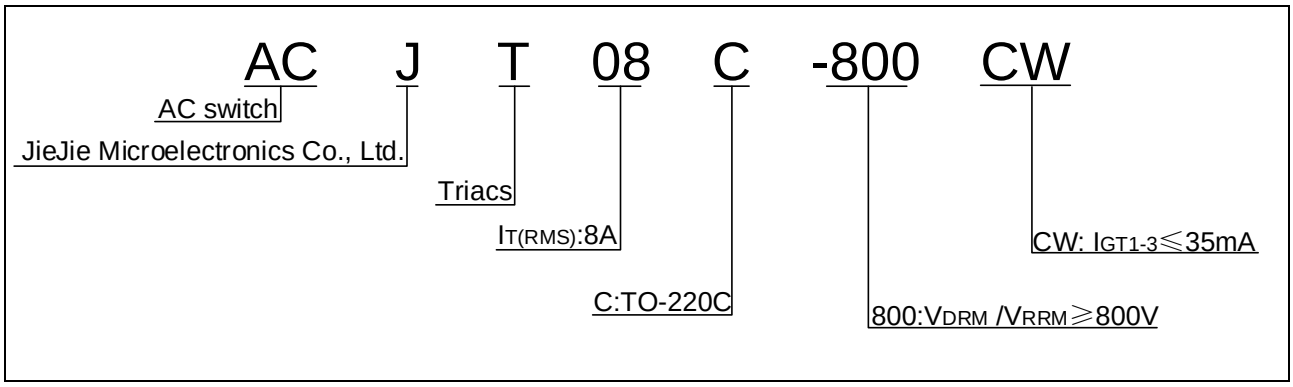
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =10A t_p=380μs	T_j=25℃	1.45	V
V_{TO}	Threshold voltage	T_j=125℃	0.78	V
R_D	Dynamic resistance	T_j=125℃	48	mΩ
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25℃	5	μA
I_{RRM}		T_j=125℃	0.5	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.5	℃/W
$R_{th(j-a)}$	junction to ambient (AC)	60	℃/W

ORDERING INFORMATION



MARKING

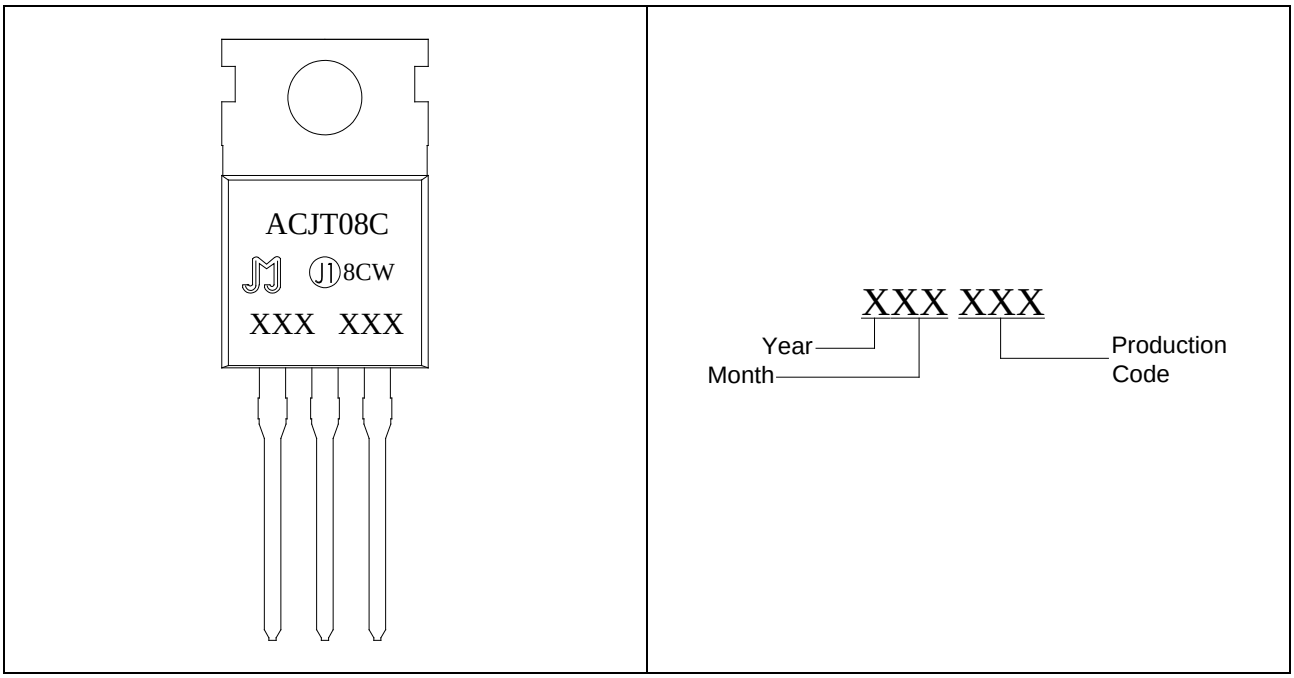


FIG.1: Maximum power dissipation versus RMS on-state current

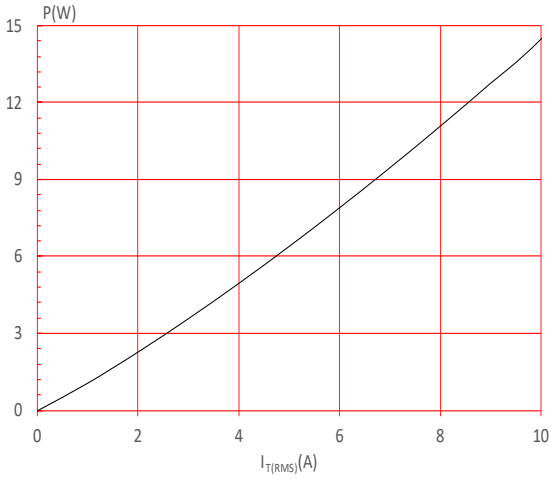


FIG.2: RMS on-state current versus case temperature

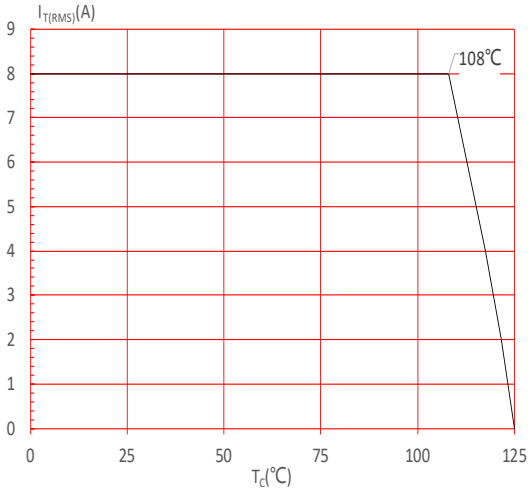


FIG.3: Surge peak on-state current versus number of cycles

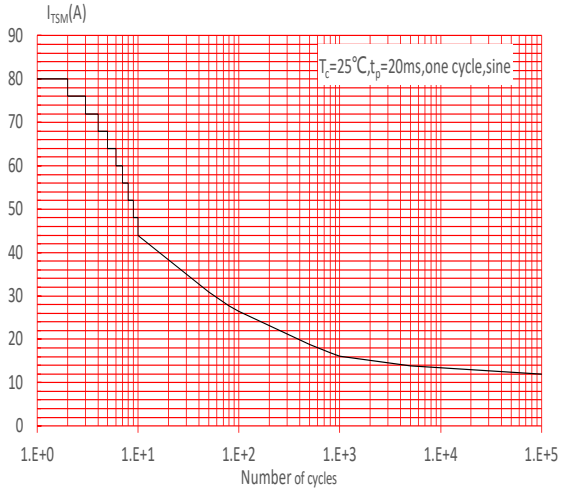


FIG.4: On-state characteristics

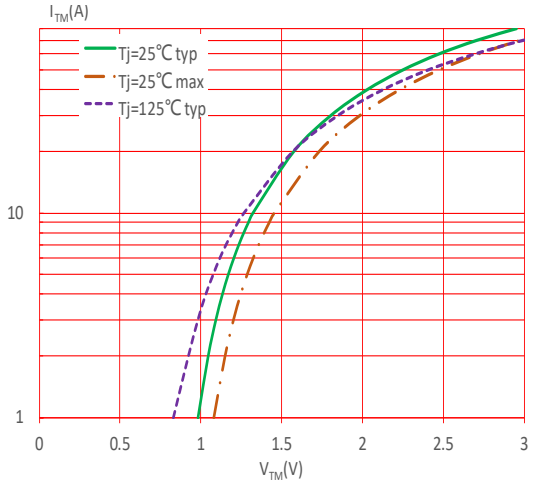


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width t_p<20ms, and corresponding value of I^2t (dI/dt<100A/μs)

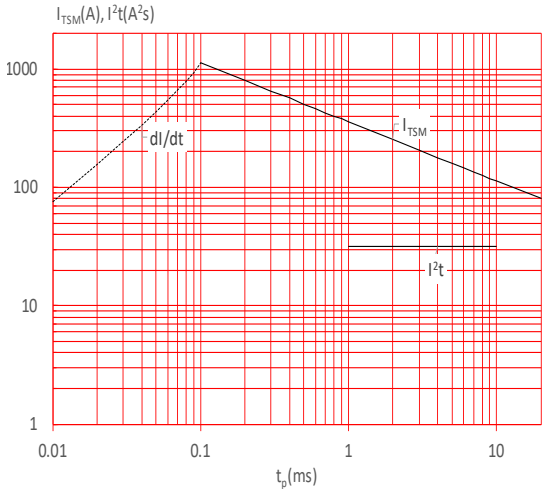


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

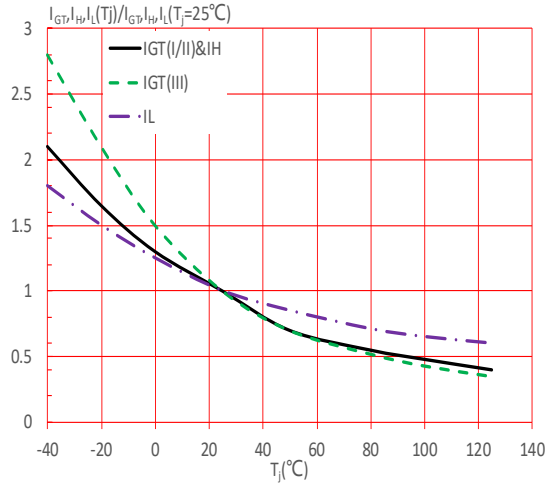
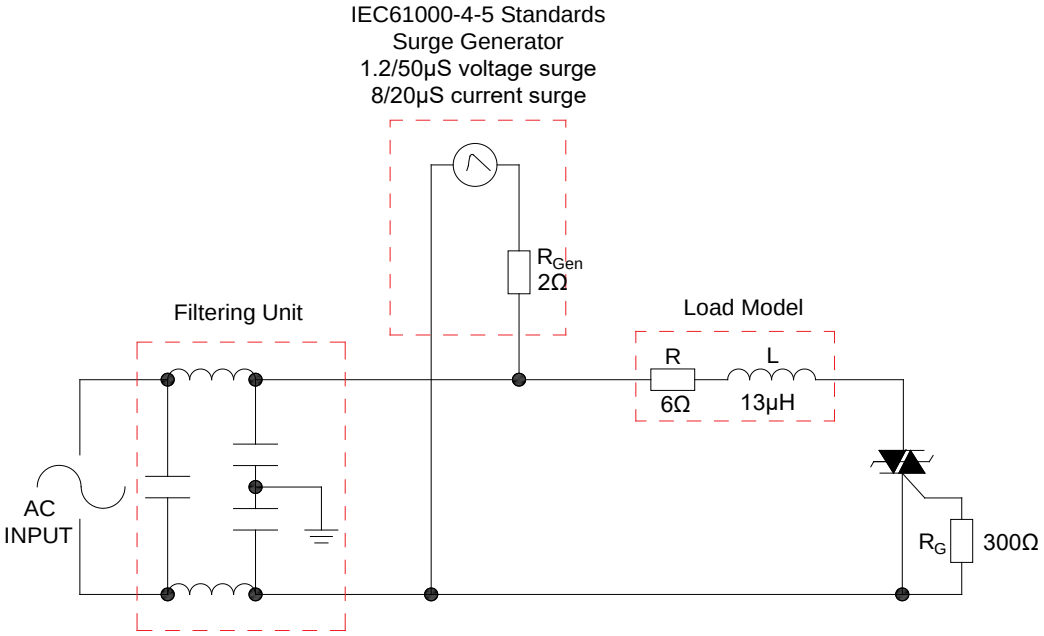


FIG.7：Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics

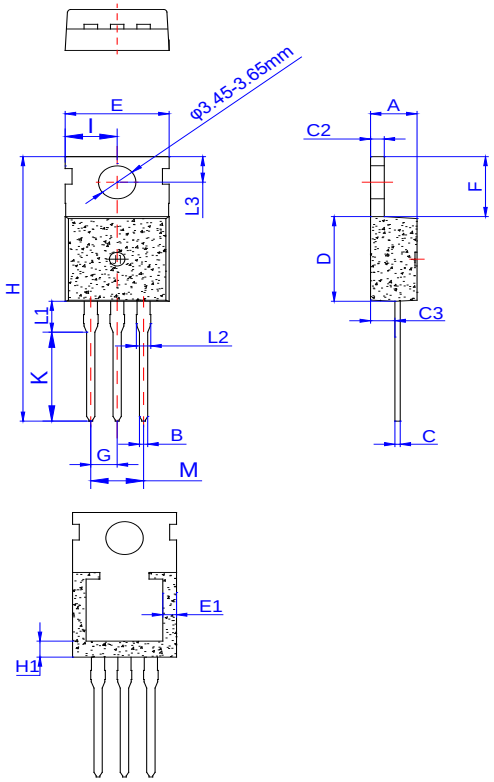
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
ACJT08C-800CW	800	35	TO-220C	50	Tube

Document Revision History

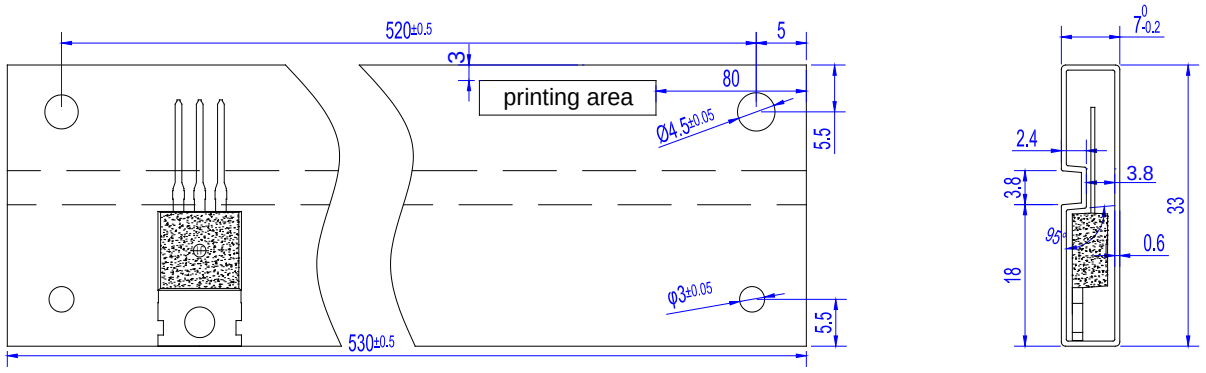
Date	Revision	Changes
Apr.13, 2023	A.1.0	Last updated
Oct.15, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.25		1.35	0.049		0.053
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.30	0.390		0.406
E1	0.80		1.20	0.031		0.047
F	6.30		6.90	0.248		0.272
G	2.40		2.70	0.094		0.106
H	28.00		29.80	1.102		1.173
H1	2.15		2.55	0.085		0.100
I	4.70		5.10	0.185		0.201
K	9.90		10.30	0.390		0.406
L1	2.70		3.30	0.106		0.130
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
M	4.80		5.20	0.189		0.205

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220C	TUBE	50	1,000	5,000

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